PATENT
Attorney Docket No.: 018867-000410US

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of:

Shuzo Fujimura et al.

Application No.: 09/328,939

Filed: June 9, 1999

For: SURFACE TREATMENT METHOD AND EQUIPMENT

Examiner: Shamim Ahmed

Art Unit: 1746

AMENDMENT

Assistant Commissioner for Patents
Washington, D.C. 20231

Sir:

In response to the Office Action mailed October 02, 2001, please amend the above-identified application as follows:

IN THE SPECIFICATION:

On page 1, line 14, replace the full paragraph with the following:

--In the manufacture of objects such as integrated circuits, processing safety and reliability have been quite important. Fabrication of integrated circuits generally requires numerous processing steps such as etching, deposition, photolithography, and others. In the manufacture of semiconductor wafers, there have been used or proposed a variety of surface treatment methods. For example, there have been several documents which reported material surface treatments using the reaction of atomic hydrogen processed by a hydrogen containing gas plasma. Japanese Patent KOKAI H7-75229 and U.S. Patent No. 5,089,441 appeared to show an ashing method of organic materials, which was carbonized by ion implant, in a hydrogen plasma in which a concentration of atomic hydrogen was increased by adding water vapor into the hydrogen plasma.--

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On page 5, line 27 replace the last full paragraph with the following:

--Among these gases, alcohol or organic acid is containing oxygen thus generating water vapor in the mixed gas plasma with hydrogen molecules. In some other gases such as silane and phosphine, they themselves are reductive. Therefore, contribution of

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